



650nm LASER DIODE COMPONENT

Features

- MQW 650nm FP LD
- High output power
- Low threshold current
- Built-in InGaAsP monitor PD
- Wide temperature range operation
(Tc= -10 to+65°C)



Applications

Light Source

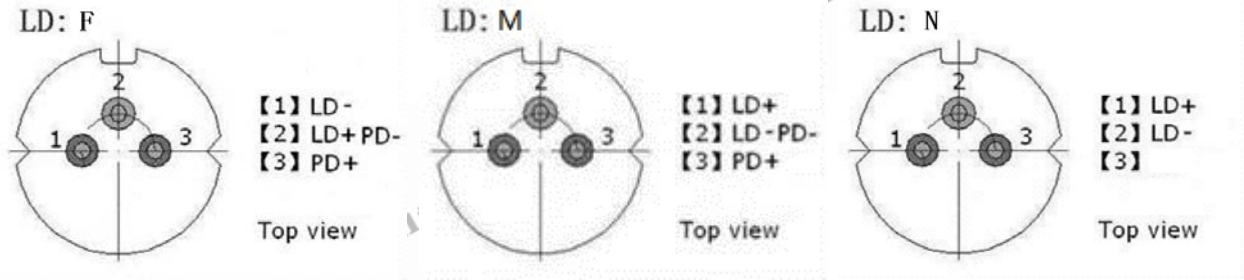
Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
LD Forward Current	IF(LD)	200	mA
LD Reverse Voltage	VR(LD)	2	V
PD Forward Current	IF(PD)	2	mA
PD Reverse Voltage	VR(PD)	25	V
Operating Temperature	TOP(LD)	-10 ~ +60	°C
Storage Temperature	TST	-40 ~ +80	°C
Soldering Temperature/Time	-	240/10	°C/S

Optical & Electrical Characteristics

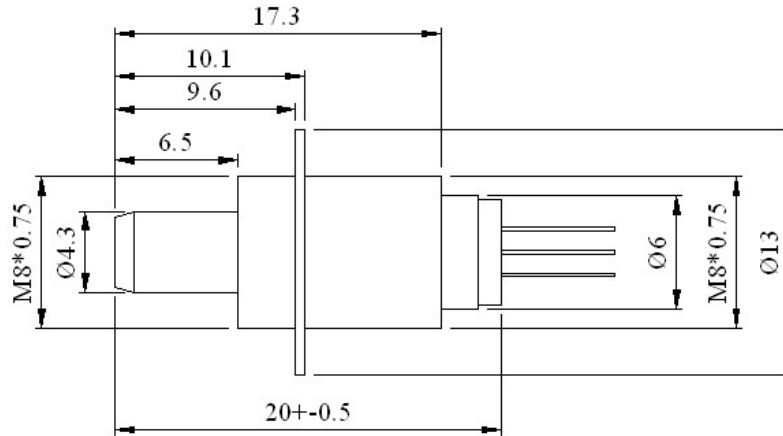
Parameter	Symbol	Min.	Typ.	Max.	Unit
Output Power	Po	1	-	20	mW
Operating Current	Iop	25	-	140	mA
Operating Voltage	Vop	-	2.2	2.8	V
Center Wavelength	λ	640	650	660	nm
Spectral Width	$\Delta\lambda$	-	-	4	nm
Monitor Current	Im	0.1	0.2	0.5	mA
Rise/ Fall Time	Tr/Tf	-	-	0.5	ns

PIN Definition



Note: F Type Pin Applicable Power 1~2mw
M Type Pin Applicable Power 1~5mw
N Type Pin Applicable Power 5~20mw

Drawing



Order Information

T650-WXXX

T	650	-W	X	X	X
Mode	Wavelength	Transfer Type	Pin Type	Connector	Power Range
	650nm	W: Plug-in	F M N	F: FC S: SC T: ST 3: FC&SC&ST	P1: >1mW P2: >2mW P20: >20mW

Additional requirements can be settled through friendly negotiation.

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